






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Mixed Circuit-Device Simulation



Outline

-  Why Mixed-mode?
-  Introduction of Crosslight Mixed-mode
-  How to Run a Mixed Circuit-Device Simulation?
-  IGBT Switching Characteristics Simulation
-  Highlights of Crosslight Mixed-mode



1. Why mixed-mode?

Compact Model:

Based on empirical formula;
Applied to IC simulation;
Difficult to obtain complex devices or complex physical events in circuit simulation;



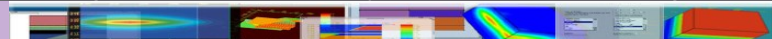
Numerical Device Model:

Based on physical models;
Applied to discrete device simulation;
Incredible complex calculations when used to replace compact model in circuit simulation;






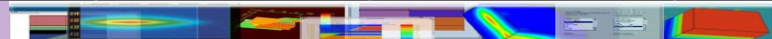
Mixed Mode:

Include one or more numerical devices in a circuit simulation;
Include several compact devices in a device simulation;



2. Introduction of Crosslight Mixed-mode

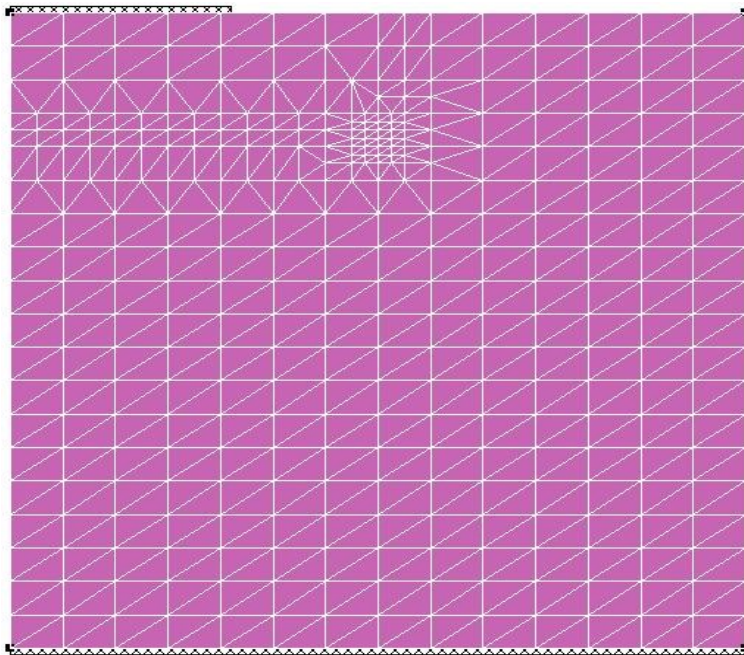
-  **Device Simulation Equations**
-  **Circuit Simulation Equations**
-  **Device-Circuit Interface Equations**



2.1. Device Simulation Equations

The non-linear system of equations for the device simulation is based on Shockley equations.

A numerical device mesh
Mesh size=M



At each node,

$$F(\phi, N, P) = 0$$

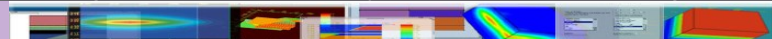
Where Φ is node voltage, N is electron density and P is hole density at each node.

Jacobian matrix for Shockley equations:

$$J(V) = \begin{bmatrix} \frac{\partial F_1}{\partial \phi_1} & \frac{\partial F_1}{\partial \phi_2} & \dots & \frac{\partial F_1}{\partial \phi_N} \\ \frac{\partial F_1}{\partial N_1} & \frac{\partial F_1}{\partial N_2} & \dots & \frac{\partial F_1}{\partial N_3} \\ \frac{\partial F_1}{\partial P_1} & \frac{\partial F_1}{\partial P_2} & \dots & \frac{\partial F_1}{\partial P_N} \\ \dots & \dots & \dots & \dots \end{bmatrix} \quad (3M \times 3M)$$

For Newton iteration:

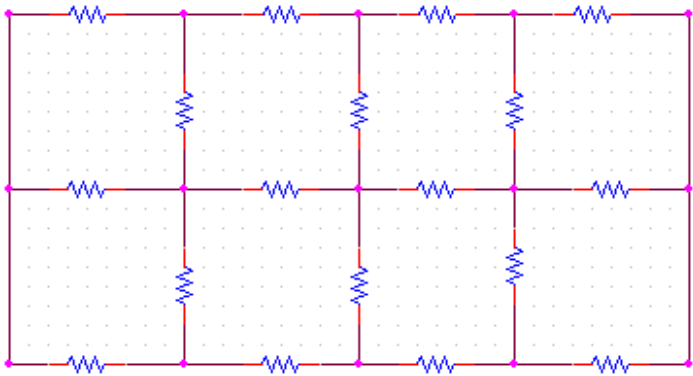
$$(V, N, P)^{i+1} = (V, N, P)^i - J^{-1}((V, N, P)^i) F((V, N, P)^i)$$



2.2. Circuit Simulation Equations

The non-linear system of equations for the circuit simulation is based on Kirchoff's current law: the sum of the currents into each node is zero.

A circuit network
Node size=N



At each node,

$$F(\mathbf{V}) = 0$$

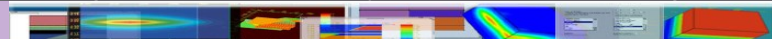
Where \mathbf{V} is the node voltage and F represent the sum of the currents into each node.

Jacobian Matrix for node current equations,

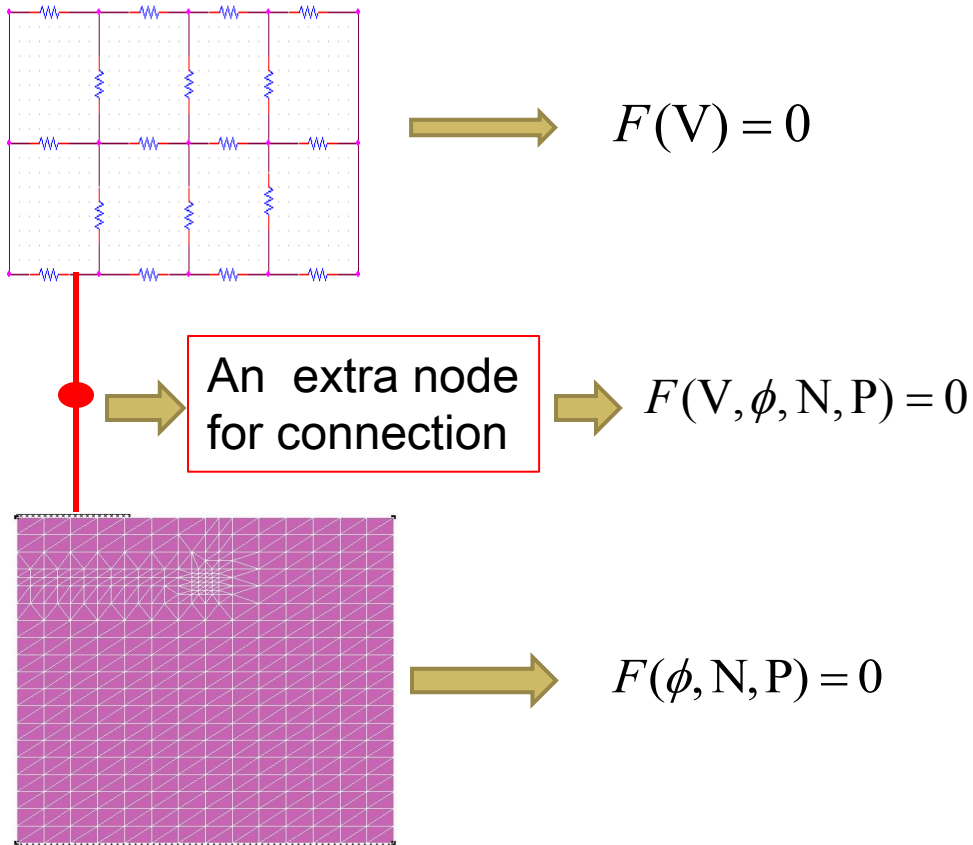
$$J(\mathbf{V}) = \begin{bmatrix} \frac{\partial F_1}{\partial V_1} & \frac{\partial F_1}{\partial V_2} & \frac{\partial F_1}{\partial V_3} \\ \dots & \dots & \dots \\ \frac{\partial F_N}{\partial V_1} & \frac{\partial F_N}{\partial V_2} & \frac{\partial F_N}{\partial V_3} \end{bmatrix} \quad (\mathbf{N} \times \mathbf{N})$$

For Newton iteration:

$$V^{i+1} = V^i - J^{-1}(V^i)F(V^i)$$

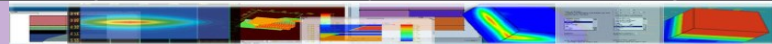


2.3. Device-Circuit Interface Equations



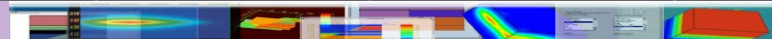
The function for the extra node is based on conservation law: the sum of the currents from circuit into the node and from mesh device into the node is zero.

Circuit node size= N
Device node size= M
Connection node size= L
Jacobian matrix order for mixed-mode= $(N+3M+L)$








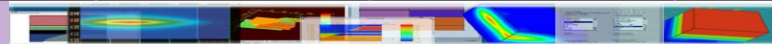
3. How to Run a Mixed Circuit-Device Simulation?

1. Build the process structure by CSUPREM
2. Set parameters for device simulation in *.sol
Define circuit following Standard SPICE-like syntax in *.cir
3. Include the external circuit(*.cir) into the device simulation file (*.sol) and link device electrodes to circuit nodes
4. Run *.sol by APSYS simulator
5. Plot simulation results by GSVIEW or CrosslightView

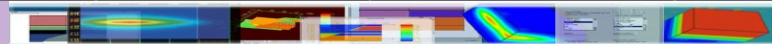
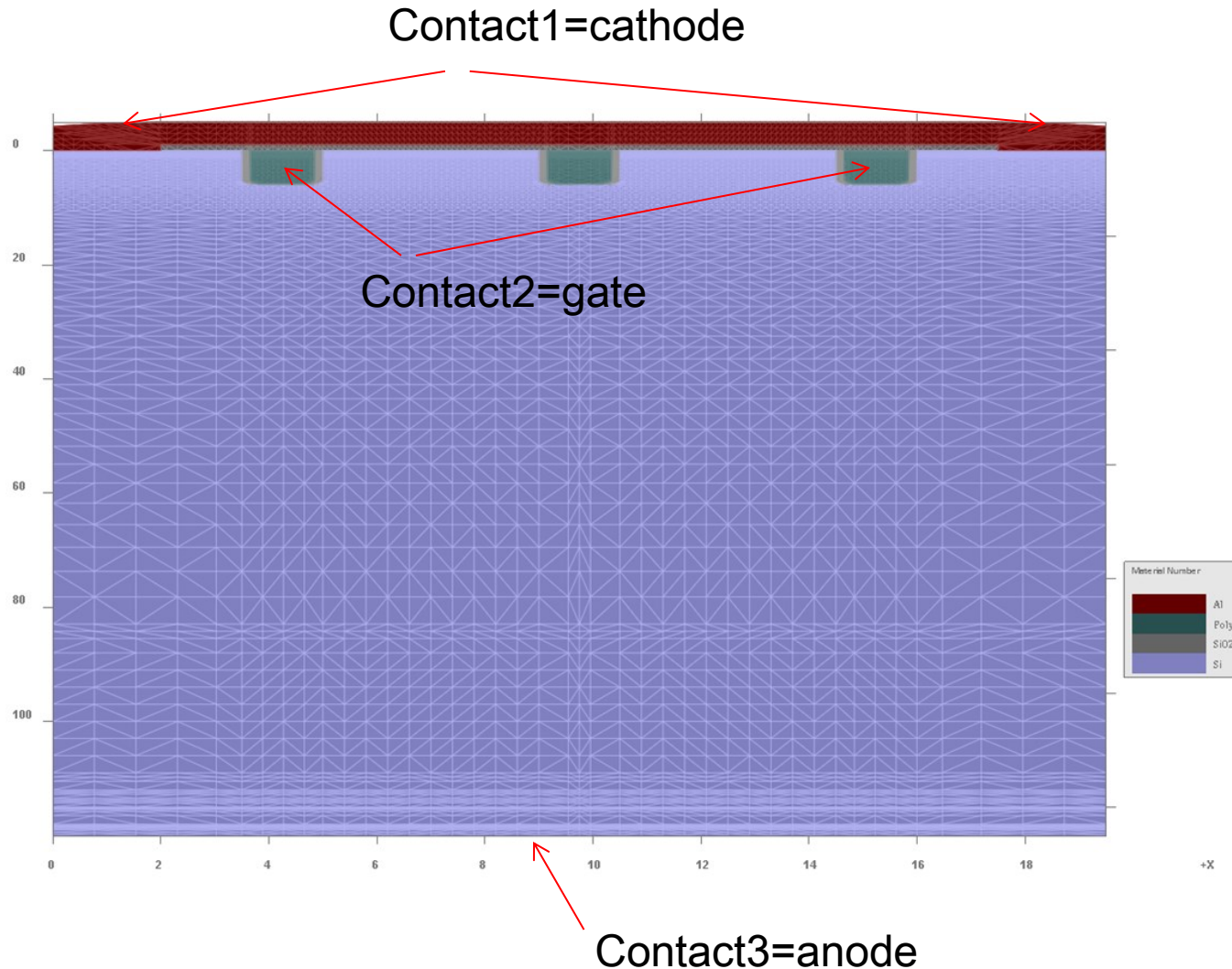


4. IGBT switching characteristics simulation

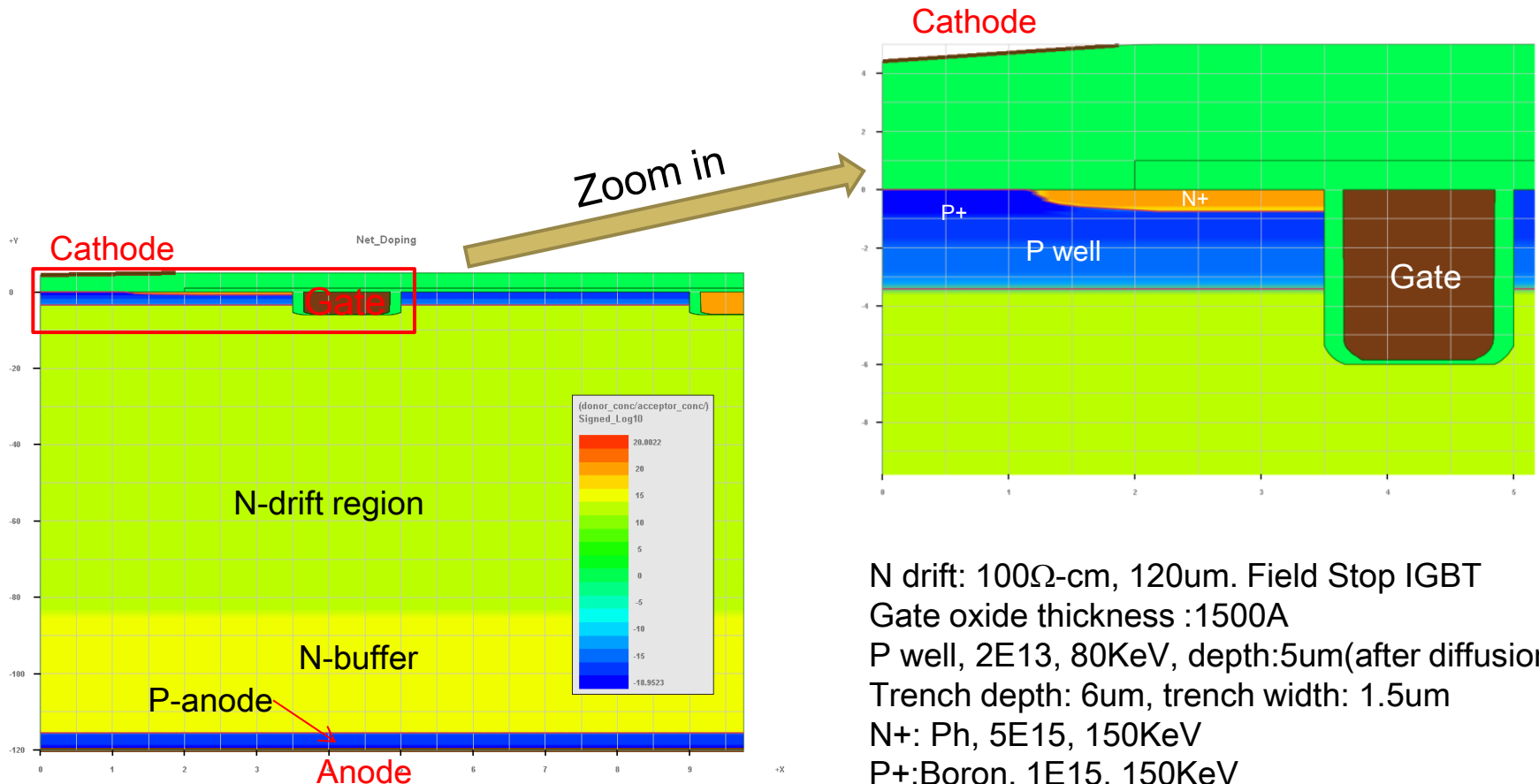
-  Build a IGBT structure by CSUPREM
-  Define IGBT dynamic test circuit
-  Link device electrodes to the circuit nodes
-  Plot simulation results
-  Analysis of IGBT switching characteristics



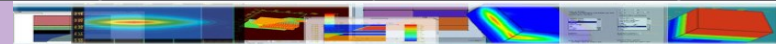
4.1. Build a IGBT structure by CSUPREM



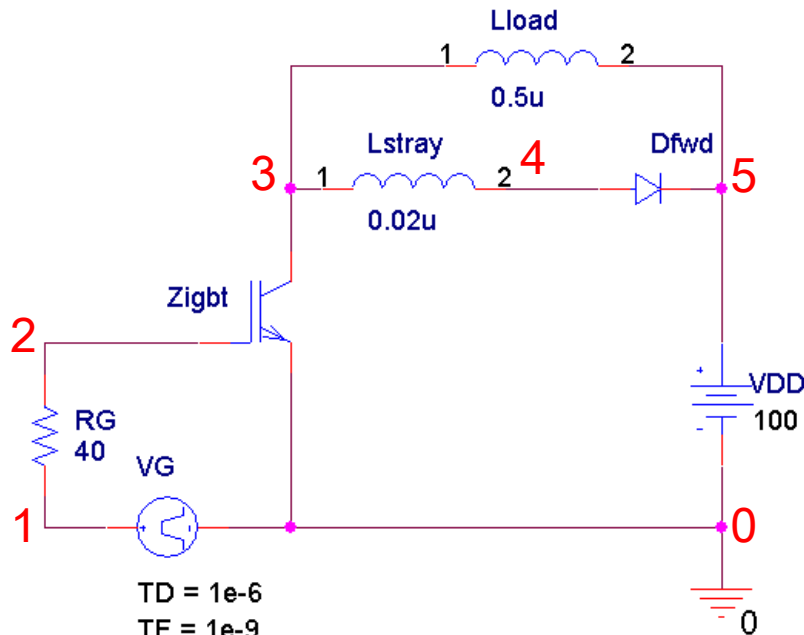
Parameters of the Simulation Structure



N drift: 100 Ω -cm, 120 μ m. Field Stop IGBT
 Gate oxide thickness :1500 \AA
 P well, 2E13, 80KeV, depth:5 μ m(after diffusion)
 Trench depth: 6 μ m, trench width: 1.5 μ m
 N+: Ph, 5E15, 150KeV
 P+:Boron, 1E15, 150KeV
 N buffer: 3 Ω -cm, 30 μ m
 P anode, doping 1e18, 2 μ m



4.2. Define IGBT dynamic test circuit

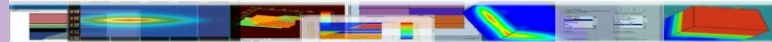


TD = 1e-6
 TF = 1e-9
 PW = 0.5e-6
 PER = 1e-6
 V1 = 0
 TR = 1e-9
 V2 = 15

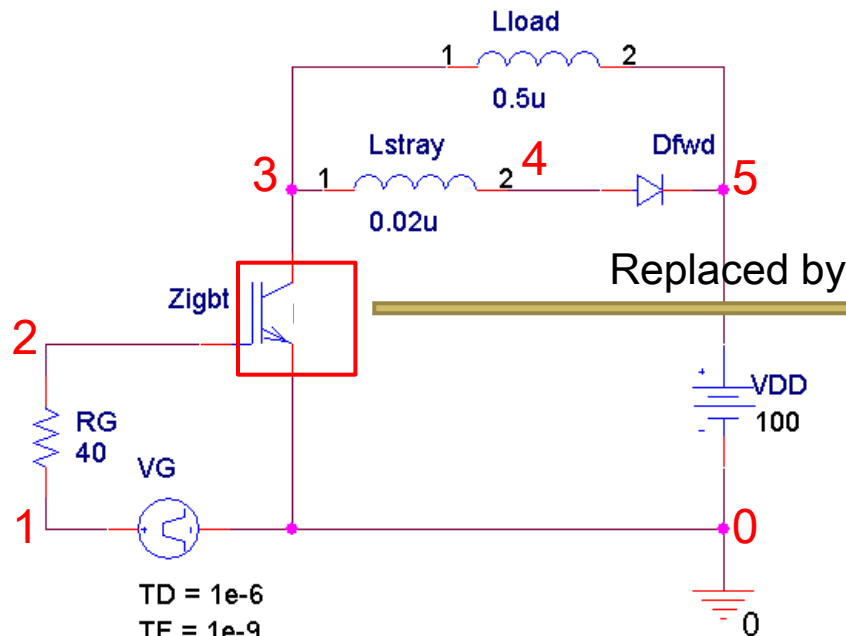
An IGBT switching test circuit(igbt_switching.cir)

```

VG 1 0 pulse(0 15 1e-6 1e-9 1e-9 2e-6 4e-6)
RG 1 2 40
Zigbt 3 2 0 IGBT
Lstray 3 4 0.02u
Dfwd 4 5 FWD 1e-5
Lload 3 5 0.5u
VDD 5 0 100
  
```



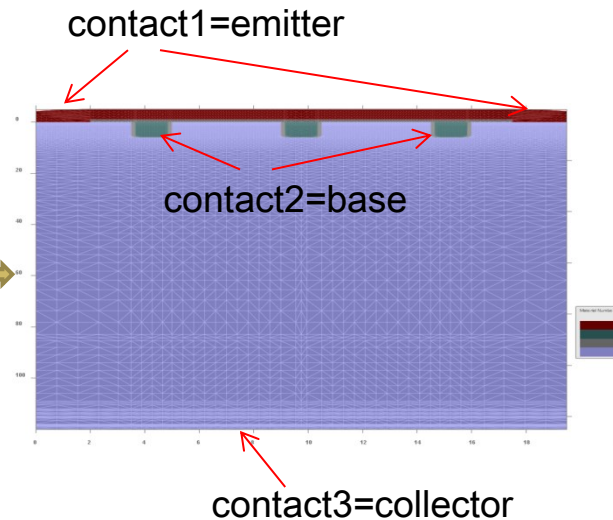
4.3. Link Device Electrodes to Circuit Nodes



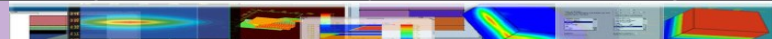
TD = 1e-6
 TF = 1e-9
 PW = 0.5e-6
 PER = 1e-6
 V1 = 0
 TR = 1e-9
 V2 = 15

```

minispice circuit_file=IGBT_switching.cir &&
z_dim=1e6 &&
spice_device_to_tcadmesh=zigbt &&
contact1_to_spice_node=0 &&
contact2_to_spice_node=2 &&
contact3_to_spice_node=3
  
```



Circuit_file: the circuit file
 Z_dim: the width of the device(not necessary in 3D simulation)
 Spice_device_to_tcadmesh: which element in the Circuit should be replaced by the mesh device
 Contact#_to_spice_node: which node in the circuit should be linked with contact#.



4.4. Plot Simulation Results

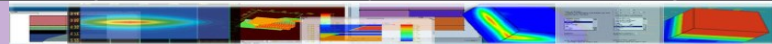
“plot_minispice” is used to plot mixed-mode simulation results, which is defined in *.plt file as follow:

```
plot_minispice variable=voltage node=1
plot_minispice variable=voltage node=2
plot_minispice variable=voltage node=3
plot_minispice variable=voltage node=4
plot_minispice variable=voltage node=5
plot_minispice variable=current node=1 element=Vg
plot_minispice variable=current node=1 element=Rg
plot_minispice variable=current node=4 element=VDD
plot_minispice variable=current node=3 element=Lload
plot_minispice variable=current node=3 element=Dfwd
plot_minispice variable=current node=3 element=Qigbt
plot_minispice variable=current node=2 element=Qigbt
plot_minispice variable=current node=5 element=Qigbt
plot_minispice variable=current node=5 element=Rs
```

X-axis: time
Y-axis: voltage at a given node

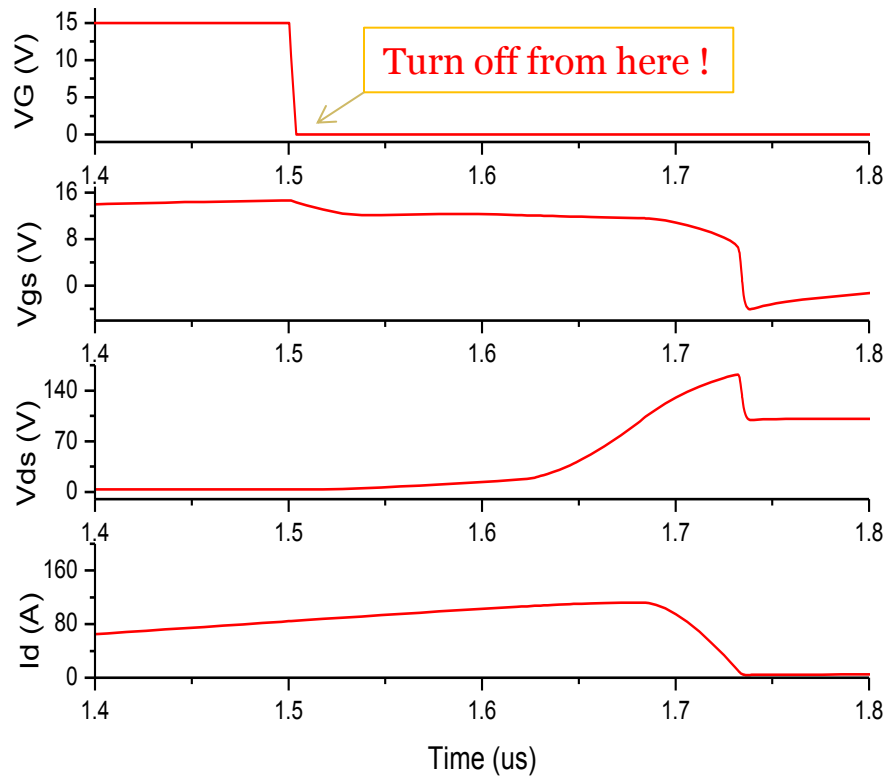
X-axis: time
Y-axis: current flowing through a given element and into the specified node.

- When plotting the current, the name of the element should be the same as the one defined in the circuit layout (case insensitive).
- Sign convention for current: current flowing INTO a node is positive.

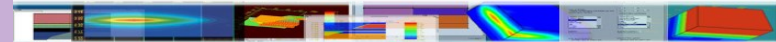
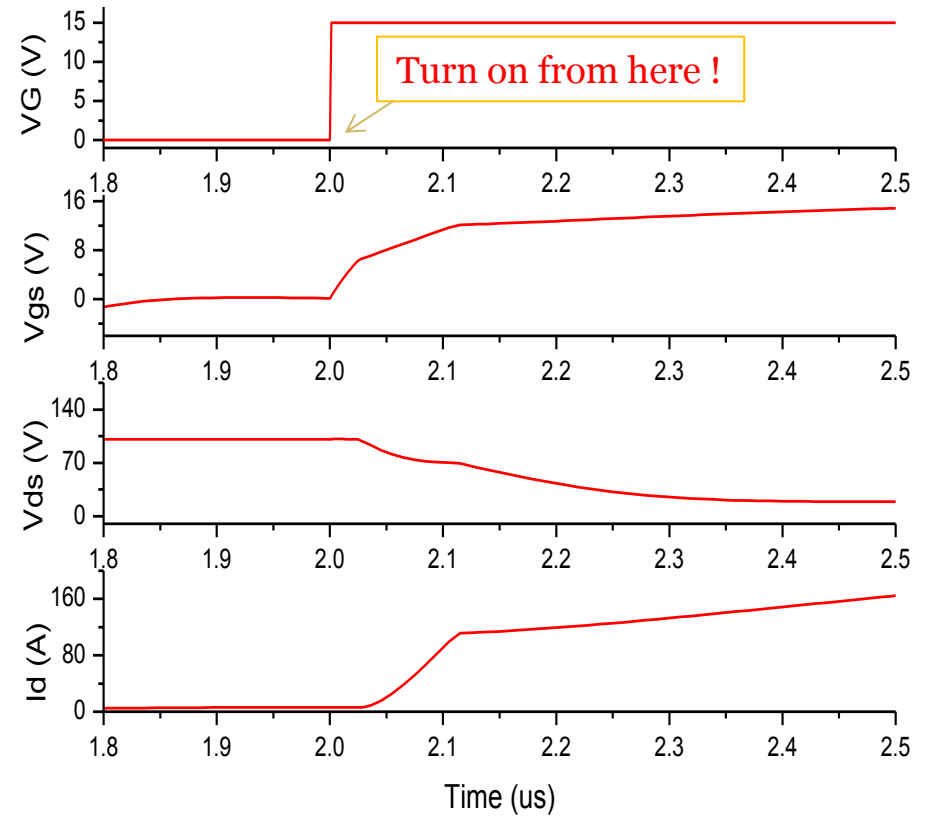


4.5. Analysis of IGBT Switching Characteristics

Typical turn off behavior



Typical turn on behavior



5. Highlights of Crosslight Mixed-mode

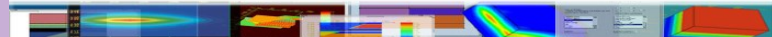
1. Ability to link a spice circuit to any APSYS device
2. DC and transient analysis supported
3. High speed and good convergence
This IGBT switching case cost 15 minutes in this PC.
Mesh size:8000

Processor: Intel(R) Core(TM) i7-2670QM CPU @ 2.20GHz 2.20 GHz

Installed memory (RAM): 8.00 GB

System type: 64-bit Operating System

4. User friendly: Standard SPICE-like syntax



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